Session Program

2–4 Jun 2008

12th RD50 Workshop

Defect Engineering & Pad Detector Characterization I

Ljubljana, Slovenia

Monday 2 June

13:30

Defect Engineering & Pad Detector Characterization I

Session | **Location:** Ljubljana, Slovenia

13:30–13:50

Electrical characterization of p- and n- type 150um epi-Si diodes irradiated by protons and neutrons

Speaker

Volodymyr Khomenkov

13:50–14:10

Annealing studies on MCz after 23 GeV proton irradiation and CCE of 150um epitaxial silicon devices

Speaker

Mrs Katharina Kaska

14:10–14:30

Systematic TCT Investigation of Equal-Double-Junctions in 24 GeV Proton Irradiated MCZ n and p-type Si Detectors

Speaker

Dr Jaakko Harkonen

14:30–14:50 **On MCz SCSI after 24 GeV/c proton irradiation**

Speaker

Donato Creanza

14:50–15:20 **Coffee Break**

15:20–15:40

Comparison of proton damage in thin FZ, MCz and epitaxial silicon detectors

Speaker

Doris Eckstein

15:40–16:00

C-V/IV and CCE measurements of MCz and FZ p and n type diodes after mixed irradiations

Speaker

Gregor Kramberger

16:00–16:30

Discussion Session: Defect Engineering & Pad Detectors (MCZ, EPI, FZ)

Speakers

Eckhart Fretwurst, Gregor Kramberger

16:30